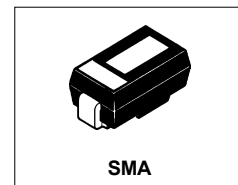




# 10MQ100N

## SCHOTTKY RECTIFIER

2.1 Amp



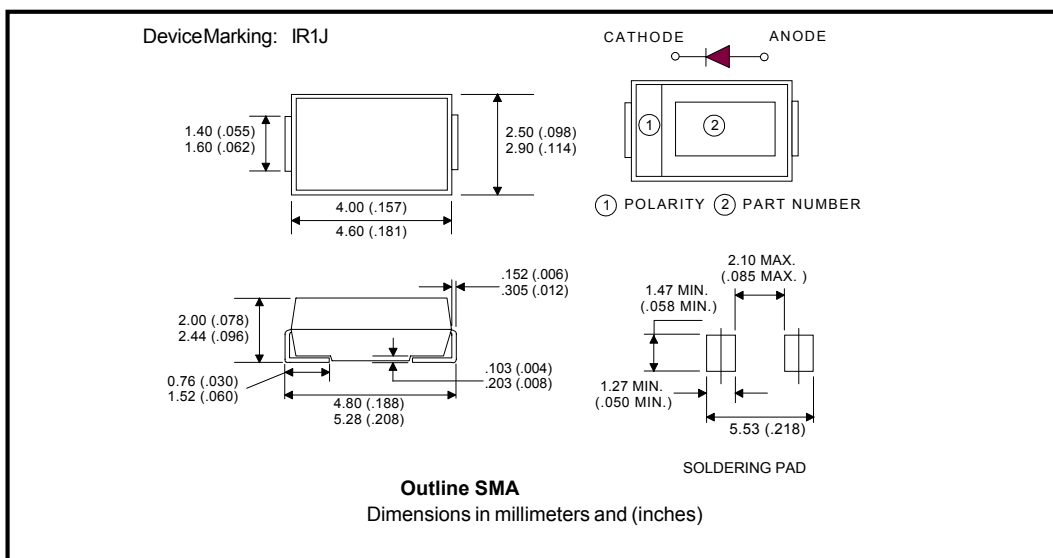
### Major Ratings and Characteristics

Characteristics	10MQ100N	Units
$I_F$ DC	2.1	A
$V_{RRM}$	100	V
$I_{FSM}$ @ $t_p=5\mu s$ sine	120	A
$V_F$ @1.5Apk, $T_J=125^\circ C$	0.68	V
$T_J$ range	-55 to 150	$^\circ C$

### Description/Features

The 10MQ100N surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability





## 10MQ100N

### Voltage Ratings

Part number	10MQ100N
$V_R$ Max. DC Reverse Voltage (V)	100
$V_{RMM}$ Max. Working Peak Reverse Voltage (V)	

### Absolute Maximum Ratings

Parameters	10MQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 4	1.5	A	50% duty cycle @ $T_L = 126^\circ\text{C}$ , rectangular wave form. On PC board 9mm <sup>2</sup> island (.013mm thick copper pad area)
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 6	120	A	Following any rated load condition and with rated $V_{RMM}$ applied
	30		
$E_{AS}$ Non-Repetitive Avalanche Energy	3.0	mJ	$T_J = 25^\circ\text{C}$ , $I_{AS} = 0.8\text{A}$ , $L = 10\text{mH}$
$I_{AR}$ Repetitive Avalanche Current	0.2	A	

### Electrical Specifications

Parameters	10MQ	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop (1) * See Fig. 1	0.78	V	@ 1A $T_J = 25^\circ\text{C}$
	0.85	V	@ 1.5A
	0.63	V	@ 1A $T_J = 125^\circ\text{C}$
	0.68	V	@ 1.5A
$I_{RM}$ Max. Reverse Leakage Current (1) * See Fig. 2	0.1	mA	$T_J = 25^\circ\text{C}$
	1	mA	$T_J = 125^\circ\text{C}$ $V_R = \text{rated } V_R$
$V_{F(TO)}$ Threshold Voltage	0.52	V	$T_J = T_J \text{ max.}$
$r_t$ Forward Slope Resistance	78.4	m $\Omega$	
$C_T$ Typical Junction Capacitance	38	pF	$V_R = 10V_{DC}$ , $T_J = 25^\circ\text{C}$ , test signal = 1Mhz
$L_S$ Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body
$dv/dt$ Max. Voltage Rate of Change (Rated $V_R$ )	10000	V/ $\mu$ s	

(1) Pulse Width < 300 $\mu$ s, Duty Cycle < 2%

### Thermal-Mechanical Specifications

Parameters	10MQ	Units	Conditions
$T_J$ Max. Junction Temperature Range (*)	-55 to 150	$^\circ\text{C}$	
$T_{stg}$ Max. Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	80	$^\circ\text{C/W}$	DC operation
wt Approximate Weight	0.07(0.002)	g(oz.)	
Case Style	SMA		Similar D-64
Device Marking	IR1J		

(\*)  $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink



10MQ100N

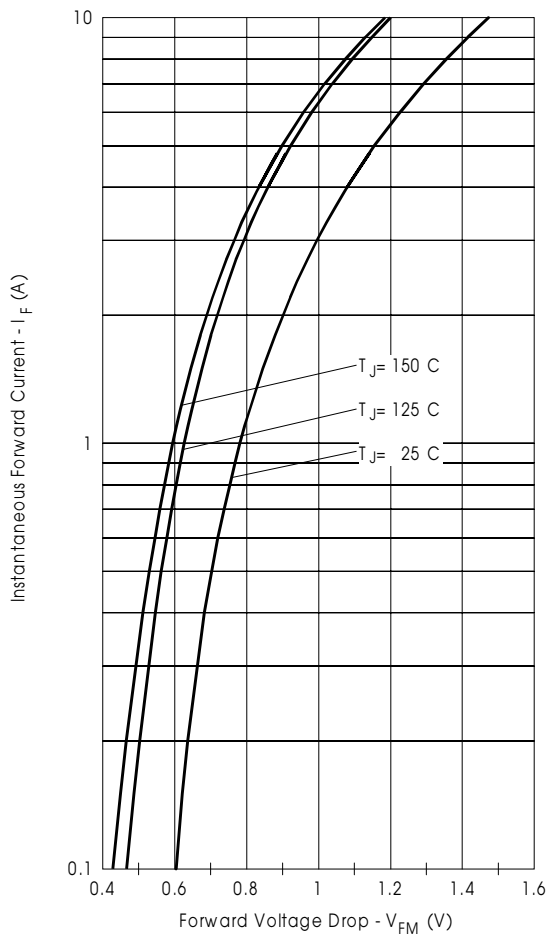


Fig. 1 - Maximum Forward Voltage Drop Characteristics

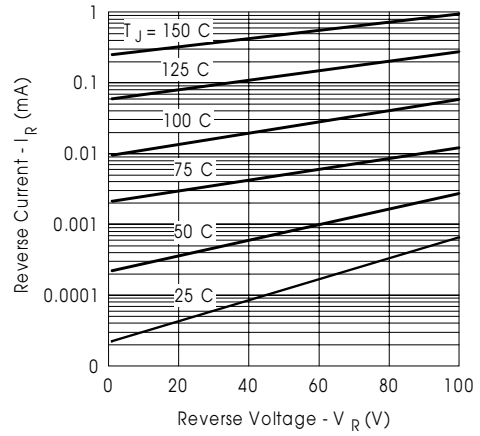


Fig. 2 - Typical Peak Reverse Current Vs. Reverse Voltage

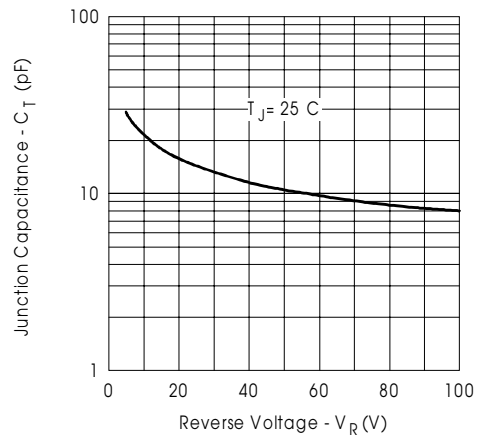


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

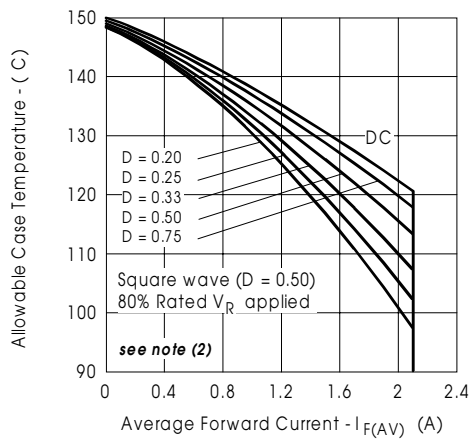


Fig. 4- Maximum Average Forward Current Vs. Allowable Lead Temperature

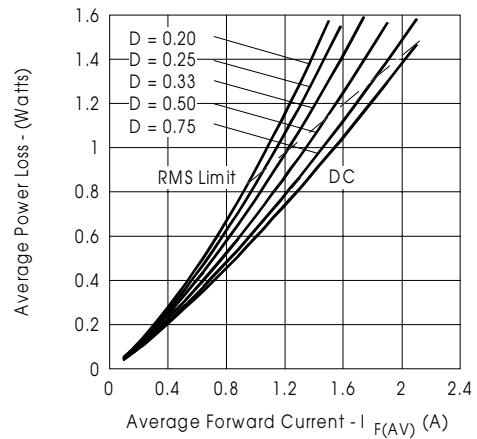


Fig. 5- Maximum Average Forward Dissipation Vs. Average Forward Current

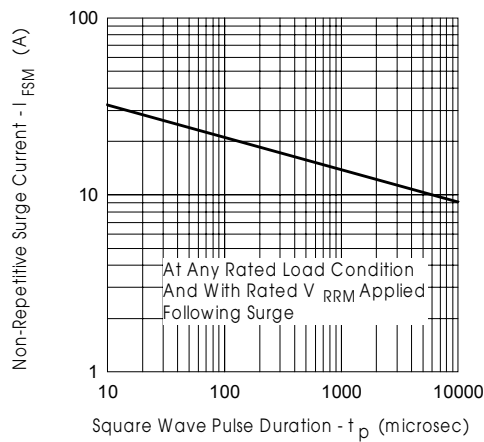


Fig. 6- Maximum Peak Surge Forward Current Vs. Pulse Duration

(2) Formula used:  $T_c = T_j - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;

$P_d$  = Forward Power Loss =  $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);

$P_{d_{REV}}$  = Inverse Power Loss =  $V_{R1} \times I_{R1} (1 - D)$ ;  $I_{R1} @ V_{R1} = 80\%$  rated  $V_R$